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# FGH25N120FTDS

## 1200 V, 25 A Field Stop Trench IGBT

### Features

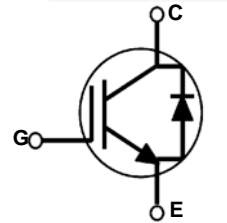
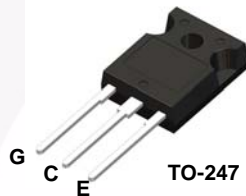
- High Speed Switching
- Low Saturation Voltage:  $V_{CE(sat)} = 1.60 \text{ V @ } I_C = 25 \text{ A}$
- High Input Impedance
- RoHS Compliant

### Applications

- Solar Inverter, UPS, Welder, PFC

### General Description

Using advanced field stop trench technology, Fairchild's 1200V trench IGBTs offer the optimum performance for hard switching application such as solar inverter, UPS, welder and PFC applications.



### Absolute Maximum Ratings

| Symbol      | Description   | Ratings     | Unit             |
|-------------|---|-------------|------------------|
| $V_{CES}$   | Collector to Emitter Voltage  | 1200        | V                |
| $V_{GES}$   | Gate to Emitter Voltage   | $\pm 25$    | V                |
| $I_C$       | Collector Current @ $T_C = 25^\circ\text{C}$                            | 50          | A                |
|             | Collector Current @ $T_C = 100^\circ\text{C}$                           | 25          | A                |
| $I_{CM(1)}$ | Pulsed Collector Current  | 75          | A                |
| $I_F$       | Diode Continuous Forward Current @ $T_C = 25^\circ\text{C}$             | 50          | A                |
|             | Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$            | 25          | A                |
| $I_{FM}$    | Diode Maximum Forward Current   | 75          | A                |
| $P_D$       | Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$                    | 313         | W                |
|             | Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$                   | 125         | W                |
| $T_J$       | Operating Junction Temperature  | -55 to +150 | $^\circ\text{C}$ |
| $T_{stg}$   | Storage Temperature Range   | -55 to +150 | $^\circ\text{C}$ |
| $T_L$       | Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds | 300         | $^\circ\text{C}$ |

**Notes:**

1: Repetitive rating: Pulse width limited by max. junction temperature

### Thermal Characteristics

| Symbol                        | Parameter                               | Typ. | Max. | Unit               |
|-------------------------------|---|------|------|--------------------|
| $R_{\theta JC}(\text{IGBT})$  | Thermal Resistance, Junction to Case    | -    | 0.4  | $^\circ\text{C/W}$ |
| $R_{\theta JC}(\text{Diode})$ | Thermal Resistance, Junction to Case    | -    | 1.25 | $^\circ\text{C/W}$ |
| $R_{\theta JA}$               | Thermal Resistance, Junction to Ambient | -    | 40   | $^\circ\text{C/W}$ |

## Package Marking and Ordering Information

| Part Number   | Top Mark      | Package | Packing Method | Reel Size | Tape Width | Quantity |
|---------------|---------------|---------|----------------|-----------|------------|----------|
| FGH25N120FTDS | FGH25N120FTDS | TO-247  | Tube           | N/A       | N/A        | 30       |

## Electrical Characteristics of the IGBT T<sub>C</sub> = 25°C unless otherwise noted

| Symbol                           | Parameter                               | Test Conditions   | Min. | Typ. | Max. | Unit |
|----------------------------------|---|---|------|------|------|------|
| <b>Off Characteristics</b>       |   |   |      |      |      |      |
| BV <sub>CES</sub>                | Collector to Emitter Breakdown Voltage  | V <sub>GE</sub> = 0 V, I <sub>C</sub> = 250 μA  | 1200 | -    | -    | V    |
| I <sub>CES</sub>                 | Collector Cut-Off Current               | V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0 V  | -    | -    | 1    | mA   |
| I <sub>GES</sub>                 | G-E Leakage Current                     | V <sub>GE</sub> = V <sub>GES</sub> , V <sub>CE</sub> = 0 V  | -    | -    | ±250 | nA   |
| <b>On Characteristics</b>        |   |   |      |      |      |      |
| V <sub>GE(th)</sub>              | G-E Threshold Voltage                   | I <sub>C</sub> = 25 mA, V <sub>CE</sub> = V <sub>GE</sub>   | 3.5  | 6    | 7.5  | V    |
| V <sub>CE(sat)</sub>             | Collector to Emitter Saturation Voltage | I <sub>C</sub> = 25 A, V <sub>GE</sub> = 15 V   | -    | 1.6  | 2    | V    |
|                                  |   | I <sub>C</sub> = 25 A, V <sub>GE</sub> = 15 V, T <sub>C</sub> = 125°C   | -    | 1.92 | -    | V    |
| <b>Dynamic Characteristics</b>   |   |   |      |      |      |      |
| C <sub>ies</sub>                 | Input Capacitance                       | V <sub>CE</sub> = 30 V, V <sub>GE</sub> = 0 V, f = 1 MHz  | -    | 4090 | -    | pF   |
| C <sub>oes</sub>                 | Output Capacitance                      |   | -    | 135  | -    | pF   |
| C <sub>res</sub>                 | Reverse Transfer Capacitance            |   | -    | 75   | -    | pF   |
| <b>Switching Characteristics</b> |   |   |      |      |      |      |
| t <sub>d(on)</sub>               | Turn-On Delay Time                      | V <sub>CC</sub> = 600 V, I <sub>C</sub> = 25 A, R <sub>G</sub> = 10 Ω, V <sub>GE</sub> = 15 V, Inductive Load, T <sub>C</sub> = 25°C  | -    | 26   | 35   | ns   |
| t <sub>r</sub>                   | Rise Time                               |   | -    | 41   | 53   | ns   |
| t <sub>d(off)</sub>              | Turn-Off Delay Time                     |   | -    | 151  | 196  | ns   |
| t <sub>f</sub>                   | Fall Time                               |   | -    | 102  | 132  | ns   |
| E <sub>on</sub>                  | Turn-On Switching Loss                  |   | -    | 1.42 | 1.84 | mJ   |
| E <sub>off</sub>                 | Turn-Off Switching Loss                 |   | -    | 1.16 | 1.5  | mJ   |
| E <sub>ts</sub>                  | Total Switching Loss                    |   | -    | 2.58 | 3.34 | mJ   |
| t <sub>d(on)</sub>               | Turn-On Delay Time                      | V <sub>CC</sub> = 600 V, I <sub>C</sub> = 25 A, R <sub>G</sub> = 10 Ω, V <sub>GE</sub> = 15 V, Inductive Load, T <sub>C</sub> = 125°C | -    | 22   | -    | ns   |
| t <sub>r</sub>                   | Rise Time                               |   | -    | 41   | -    | ns   |
| t <sub>d(off)</sub>              | Turn-Off Delay Time                     |   | -    | 163  | -    | ns   |
| t <sub>f</sub>                   | Fall Time                               |   | -    | 136  | -    | ns   |
| E <sub>on</sub>                  | Turn-On Switching Loss                  |   | -    | 2.04 | -    | mJ   |
| E <sub>off</sub>                 | Turn-Off Switching Loss                 |   | -    | 1.58 | -    | mJ   |
| E <sub>ts</sub>                  | Total Switching Loss                    |   | -    | 3.62 | -    | mJ   |
| Q <sub>g</sub>                   | Total Gate Charge                       | V <sub>CE</sub> = 600 V, I <sub>C</sub> = 25 A, V <sub>GE</sub> = 15 V  | -    | 169  | 225  | nC   |
| Q <sub>ge</sub>                  | Gate to Emitter Charge                  |   | -    | 33   | 44   | nC   |
| Q <sub>gc</sub>                  | Gate to Collector Charge                |   | -    | 78   | 104  | nC   |

**Electrical Characteristics of the Diode** T<sub>C</sub> = 25°C unless otherwise noted

| Symbol          | Parameter                           | Test Conditions  | Min.                   | Typ. | Max | Unit |    |
|-----------------|-------------------------------------|--|------------------------|------|-----|------|----|
| V <sub>FM</sub> | Diode Forward Voltage               | I <sub>F</sub> = 25 A                                    | T <sub>C</sub> = 25°C  | -    | 2.5 | 3.5  | V  |
|                 |                                     |  | T <sub>C</sub> = 125°C | -    | 2.3 | -    |    |
| t <sub>rr</sub> | Diode Reverse Recovery Time         | I <sub>F</sub> = 25 A,<br>di <sub>F</sub> /dt = 200 A/μs | T <sub>C</sub> = 25°C  | -    | 411 | 535  | ns |
|                 |                                     |  | T <sub>C</sub> = 125°C | -    | 496 | -    |    |
| I <sub>rr</sub> | Diode Peak Reverse Recovery Current | I <sub>F</sub> = 25 A,<br>di <sub>F</sub> /dt = 200 A/μs | T <sub>C</sub> = 25°C  | -    | 5.2 | 6.8  | A  |
|                 |                                     |  | T <sub>C</sub> = 125°C | -    | 6.9 | -    |    |
| Q <sub>rr</sub> | Diode Reverse Recovery Charge       | I <sub>F</sub> = 25 A,<br>di <sub>F</sub> /dt = 200 A/μs | T <sub>C</sub> = 25°C  | -    | 1.1 | 1.82 | μC |
|                 |                                     |  | T <sub>C</sub> = 125°C | -    | 1.7 | -    |    |



## Typical Performance Characteristics

Figure 1. Typical Output Characteristics

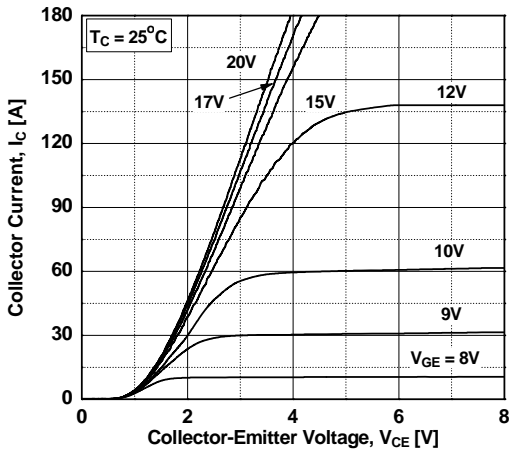


Figure 2. Typical Output Characteristics

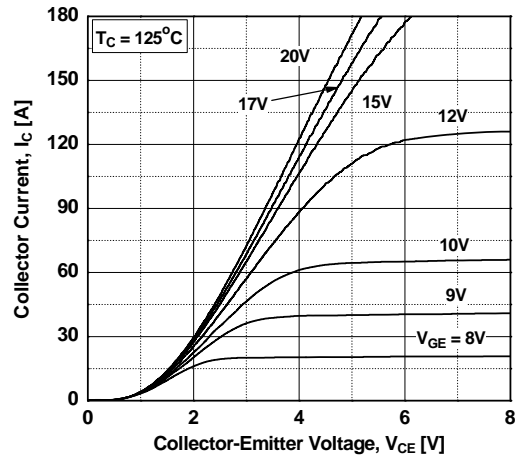


Figure 3. Typical Saturation Voltage Characteristics

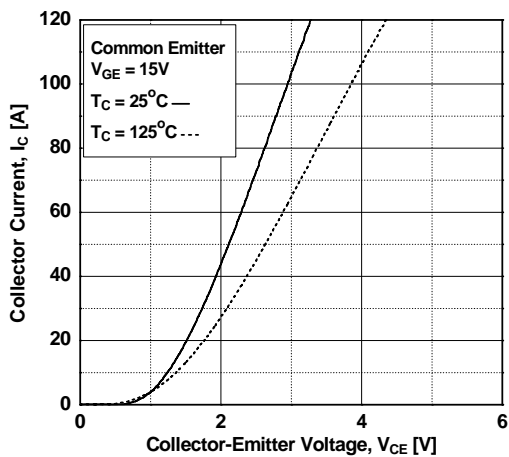


Figure 4. Transfer Characteristics

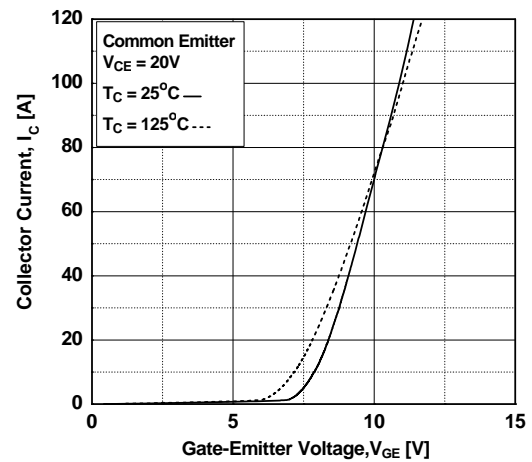


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

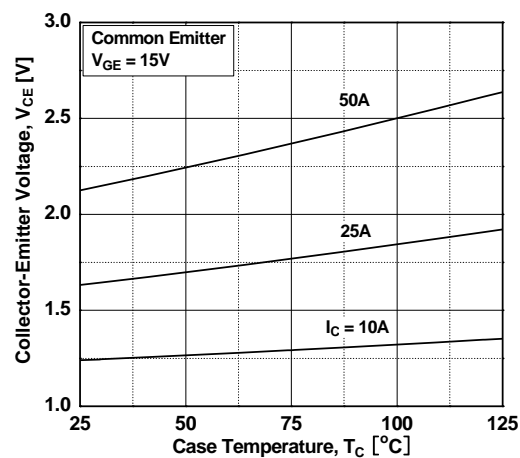
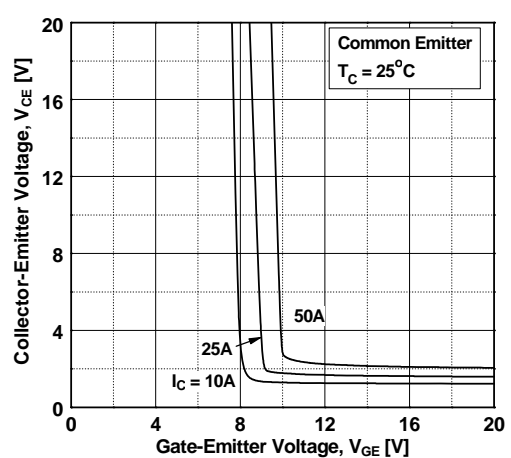


Figure 6. Saturation Voltage vs. Vge



## Typical Performance Characteristics

Figure 7. Saturation Voltage vs.  $V_{GE}$

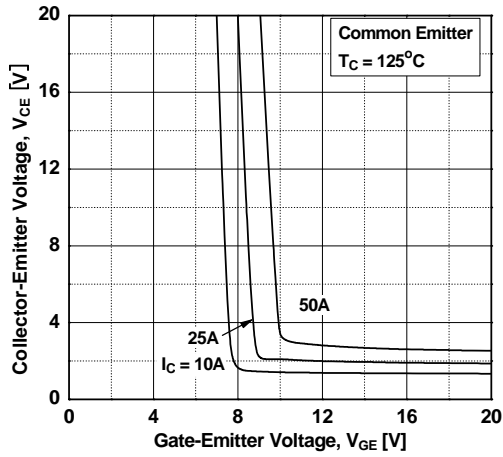


Figure 8. Load Current vs. Frequency

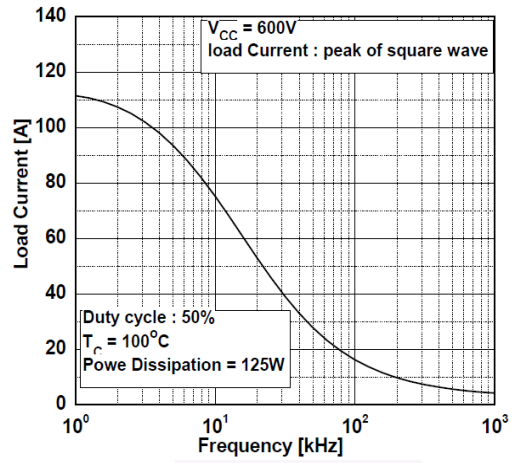


Figure 9. Capacitance Characteristics

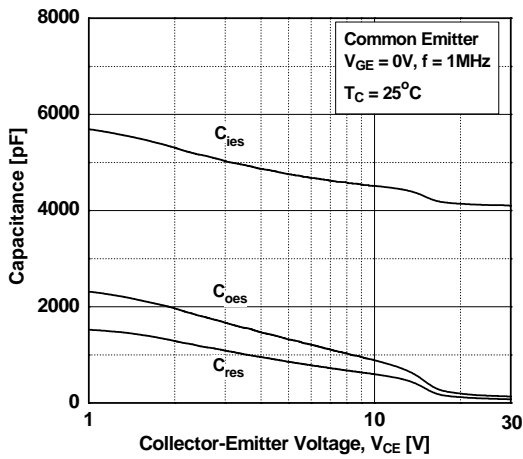


Figure 10. Gate Charge Characteristics

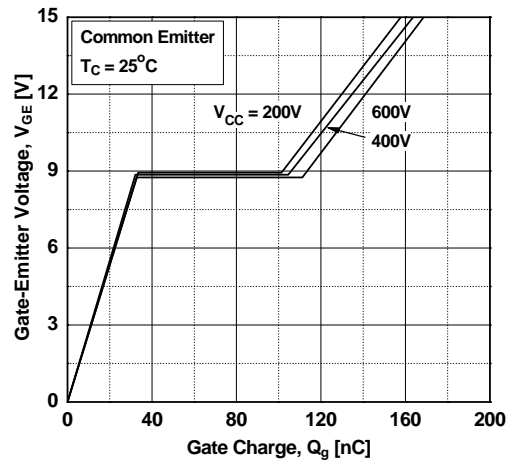


Figure 11. SOA Characteristics Gate Resistance

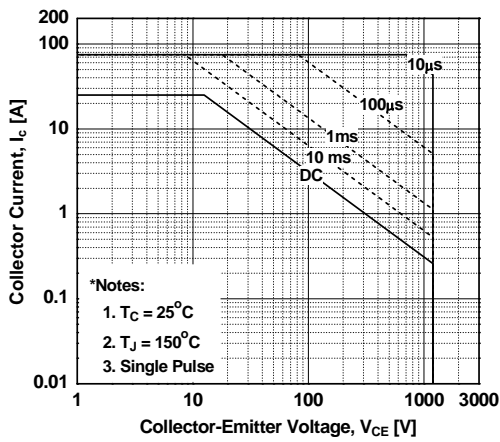
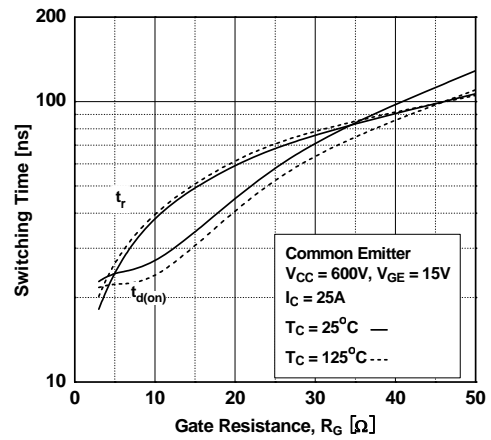
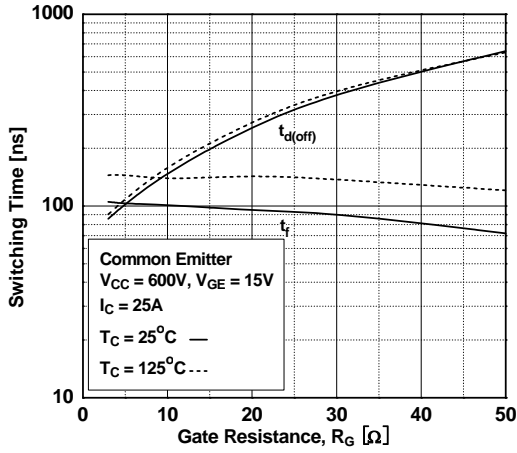


Figure 12. Turn-on Characteristics vs. Gate Resistance

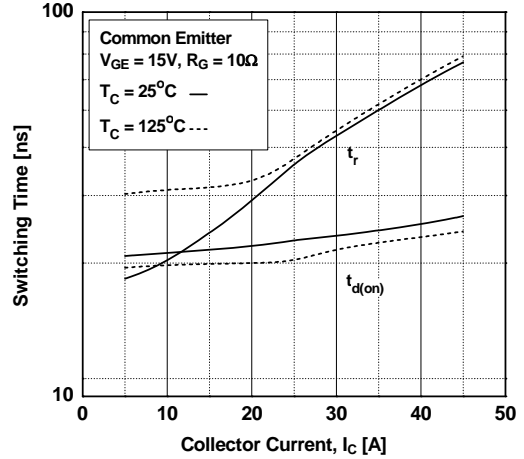


## Typical Performance Characteristics

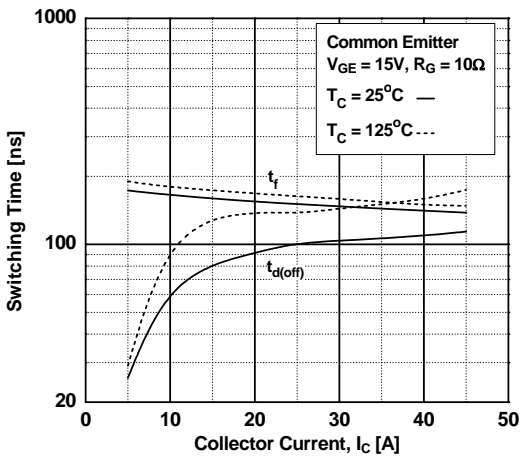
**Figure 13. Turn-off Characteristics vs. Gate Resistance**



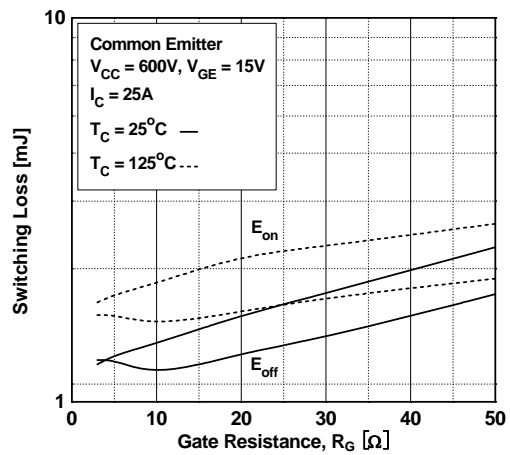
**Figure 14. Turn-on Characteristics vs. Collector Current**



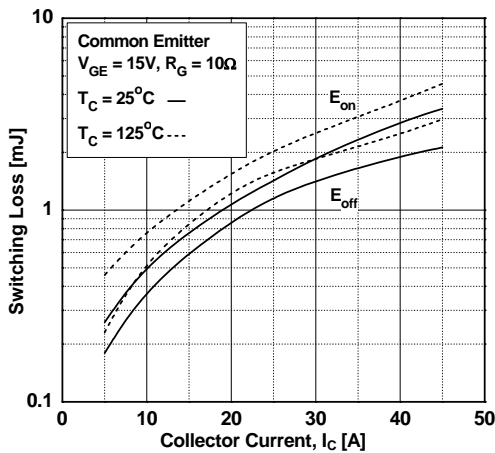
**Figure 15. Turn-off Characteristics vs. Collector Current**



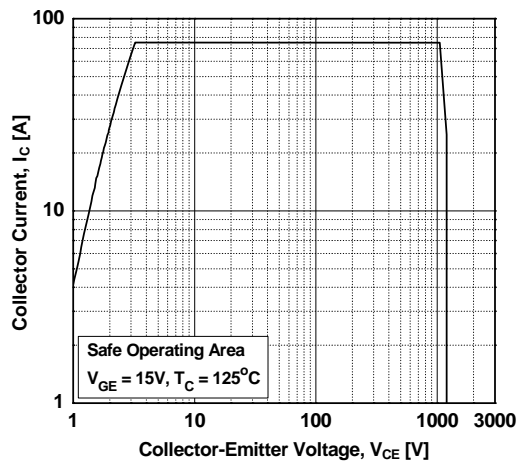
**Figure 16. Switching Loss vs. Gate Resistance**



**Figure 17. Switching Loss vs. Collector Current**



**Figure 18. Turn off Switing SOA Characteristics**



## Typical Performance Characteristics

Figure 19. Forward Characteristics

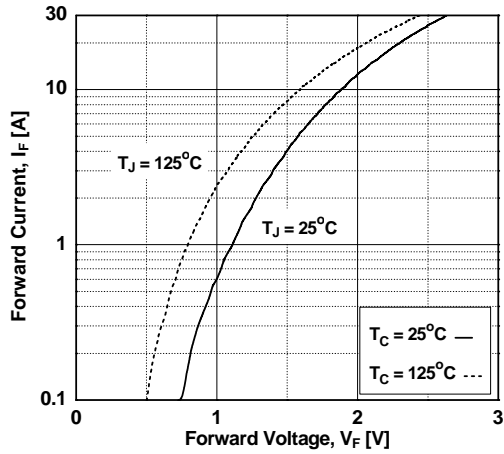


Figure 20. Reverse Recovery Current

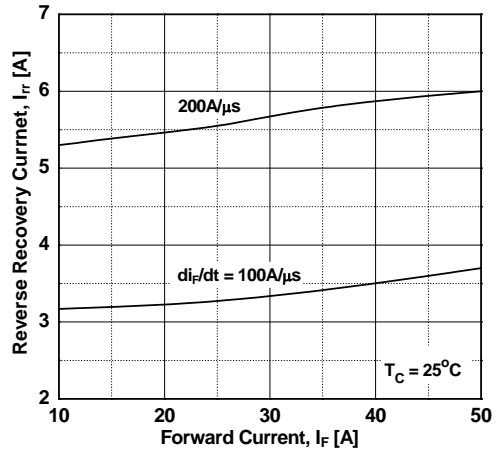


Figure 21. Stored Charge

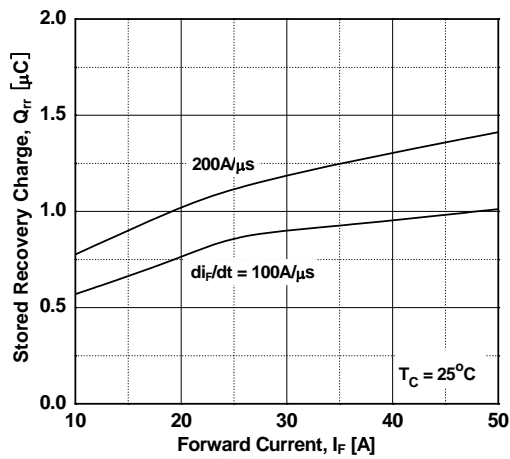


Figure 22. Reverse Recovery Time

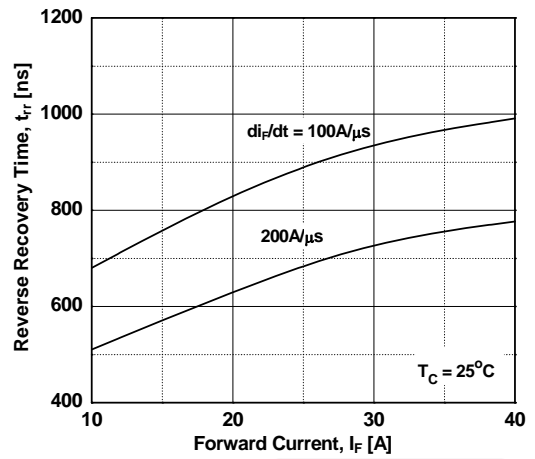
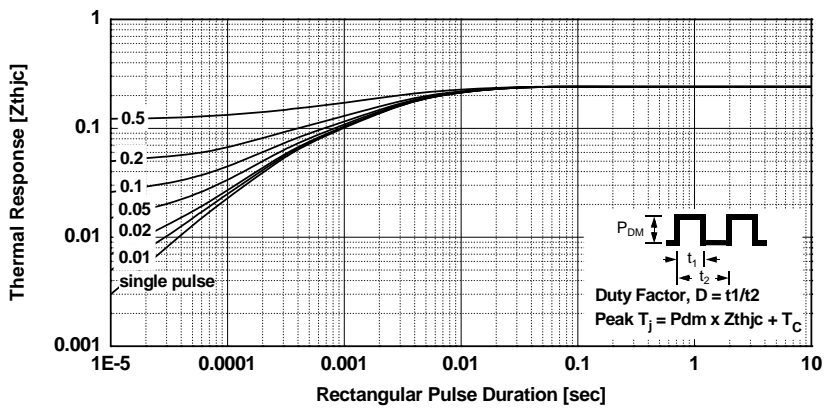
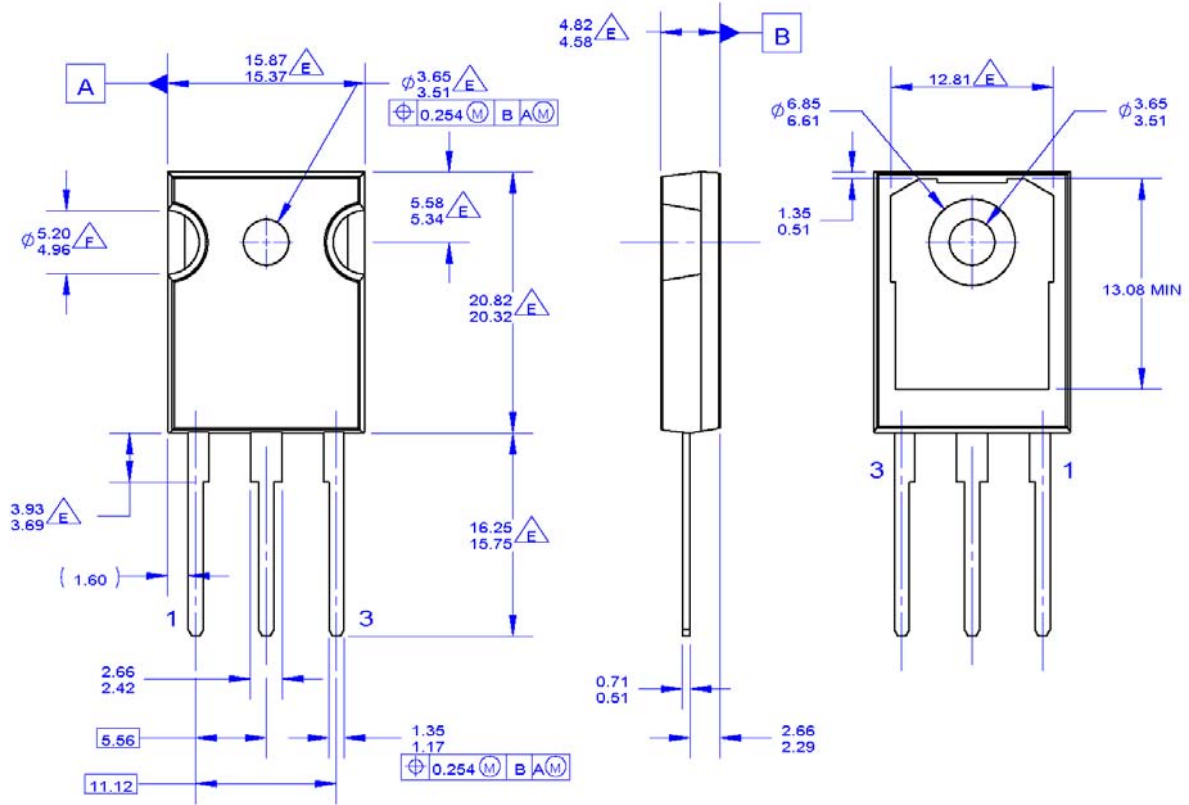


Figure 23. Transient Thermal Impedance of IGBT





**Mechanical Dimensions**



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- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5 - 1994

- DOES NOT COMPLY JEDEC STANDARD VALUE
- NOTCH MAY BE SQUARE
- G. DRAWING FILENAME: MKT-TO247A03\_REV03

**Figure 24. TO-247 3L - TO-247,MOLDED,3 LEAD,JEDEC VARIATION AB**

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| AX-CAP®*                 | FRFET®  | PowerXS™                   | <b>SYSTEM</b> ®* |
| BitSiC™                  | Global Power Resource <sup>SM</sup>             | Programmable Active Droop™ | <b>GENERAL</b>   |
| Build it Now™            | GreenBridge™                                    | QFET®                      | TinyBoost®       |
| CorePLUS™                | Green FPS™                                      | QS™                        | TinyBuck®        |
| CorePOWER™               | Green FPS™ e-Series™                            | Quiet Series™              | TinyCalc™        |
| CROSSVOLT™               | Gmax™   | RapidConfigure™            | TinyLogic®       |
| CTL™                     | GTO™  |                            | TINYOPTO™        |
| Current Transfer Logic™  | IntelliMAX™                                     |                            | TinyPower™       |
| DEUXPEED®                | ISOPLANAR™                                      |                            | TinyPWM™         |
| Dual Cool™               | Marking Small Speakers Sound Louder and Better™ |                            | TinyWire™        |
| EcoSPARK®                | MegaBuck™                                       |                            | TranSiC™         |
| EfficientMax™            | MICROCOUPLER™                                   |                            | TriFault Detect™ |
| ESBC™                    | MicroFET™                                       |                            | TRUECURRENT®*    |
| <b>F</b> ®               | MicroPak™                                       |                            | µSerDes™         |
| Fairchild®               | MicroPak2™                                      |                            | <b>SerDes</b>    |
| Fairchild Semiconductor® | MillerDrive™                                    |                            | UHC®             |
| FACT Quiet Series™       | MotionMax™                                      |                            | Ultra FRFET™     |
| FACT®                    | mWSaver®  |                            | UniFET™          |
| FAST®                    | OptoHiT™  |                            | VCX™             |
| FastvCore™               | OPTOLOGIC®                                      |                            | VisualMax™       |
| FETBench™                | OPTOPLANAR®                                     |                            | VoltagePlus™     |
| FPS™                     |   |                            | XS™              |

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| Preliminary              | First Production      | Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design. |
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